



20V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
-20V	200mΩ @ V _{GS} = -4.5V	-2.3A

Description

This new generation of high density MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

Applications

- DC DC Converters
- **Power Management Functions**
- **Disconnect Switches**
- Motor Control

Features and Benefits

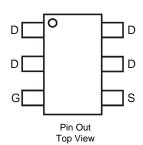
- Low On-resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

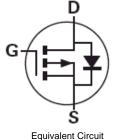
Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.018 grams (Approximate)









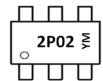
Ordering Information (Note 4)

Part Number	Reel Size (inch)	Tape Width (mm)	Quantity Per Reel
ZXM62P02E6TA	7	8	3,000
ZXM62P02E6TC	13	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and -1000ppm antimony compounds.
 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



2P02 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: C = 2015) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Date Code It												
Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026
Code	С	D	E	F	G	Н	I	J	K	L	M	N
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Absolute Maximum Ratings

C	Characteristic		Symbol	Value	Unit	
Drain-Source Voltage			V _{DSS}	-20	V	
Gate-Source Voltage			V _{GSS}	±12	V	
Continuos Brain Commit		$T_A = +25^{\circ}C \text{ (Note 6)}$		-2.3	^	
Continuous Drain Current	$V_{GS} = -4.5V$	$T_A = +70^{\circ}C \text{ (Note 6)}$	I _D	-1.7	A	
Pulsed Drain Current		(Note 7)	I _{DM}	-13	Α	
Continuous Source Current	(Body Diode)	(Note 6)	Is	-1.9	Α	
Pulsed Source Current (Body Diode) ((Note 7)	I _{SM}	-13	Α	
Power Dissipation at T _A = +25°C Linear Derating Factor		(Note 5)	P _D	1.1 8.8	W mW/°C	
Power Dissipation at T _A = +25 Linear Derating Factor	o°C	(Note 6)	P _D	1.7 13.7	W mW/°C	
Operating and Storage Tempe	rature Range		T _J , T _{STG}	-55 to +150	°C	

Thermal Resistance

Characteristic	Symbol	Value	Unit	
lunction to Ambient	(Note 5)	9	113	0000
Junction to Ambient	(Note 6)	$R_{ heta JA}$	73	°C/W

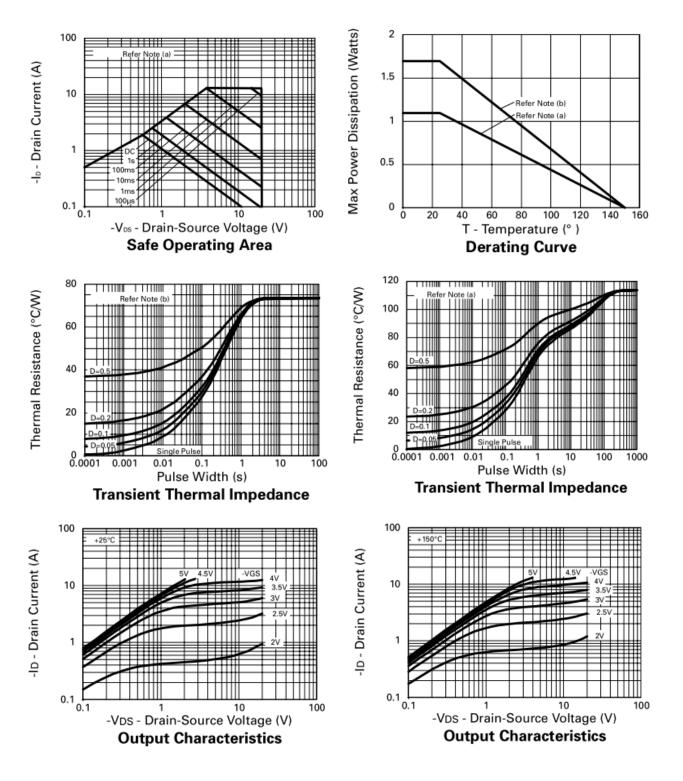
Electrical Characteristics (@T_A = +25°C, unless otherwise stated.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
STATIC			-	I.		
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$I_D = -250 \mu A, V_{GS} = 0 V$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
Gate Threshold Voltage	V _{GS(TH)}	-0.7	_	_	V	$I_D = -250 \mu A, V_{DS} = V_{GS}$
Otatia Basia Course On Besistance (Nete 9)				0.2	0	V _{GS} = -4.5V, I _D = -1.6A
Static Drain-Source On-Resistance (Note 8)	R _{DS(ON)}	_	_	0.375	Ω	V _{GS} = -2.7V, I _D = -0.8A
Forward Transconductance (Note 10)	g fs	1.5	_	_	S	V _{DS} = -10V, I _D = -0.8A
DYNAMIC (Note 10)						
Input Capacitance	C _{iss}	_	320	_	pF	
Output Capacitance	Coss	_	150	_	pF	$V_{DS} = -15V, V_{GS} = 0V$ -f = 1MHz
Reverse Transfer Capacitance	C _{rss}	_	75	_	pF	-1 = 11VII 12
SWITCHING (Notes 9 and10)			•	•		
Total Gate Charge	Qg	_	_	5.8	nC	V _{DS} = -16V, V _{GS} = -4.5V
Gate-Source Charge	Qgs	_	_	1.25	nC	I _D = -1.6A
Gate-Drain Charge	Q_{gd}	_	_	2.8	nC	(Refer to test circuit)
Turn-On Delay Time	t _{D(ON)}	_	4.1	_	ns	
Turn-On Rise Time	t _R	_	15.4	_	ns	$V_{DD} = -10V$, $I_D = -1.6A$, $R_G = 6\Omega$,
Turn-Off Delay Time	t _{D(OFF)}	_	12.0	_	ns	$R_D = 6.1\Omega$ (Refer to test circuit)
Turn-Off Fall Time	t _F	_	19.2	_	ns	(Note: to took on oak)
SOURCE-DRAIN DIODE			•	•		
Diode Forward Voltage (Note 8)	V _{SD}	_		-0.95	V	T _J = +25°C, I _S =-1.6A, V _{GS} =0V
Reverse recovery time (Note 10)	t _{RR}	_	22.5	_	ns	T _{.I} = +25°C, I _F =-1.6A,
Reverse recovery charge (Note 10)	Q _{RR}	_	10.4	_	nC	di/dt= 100A/μs

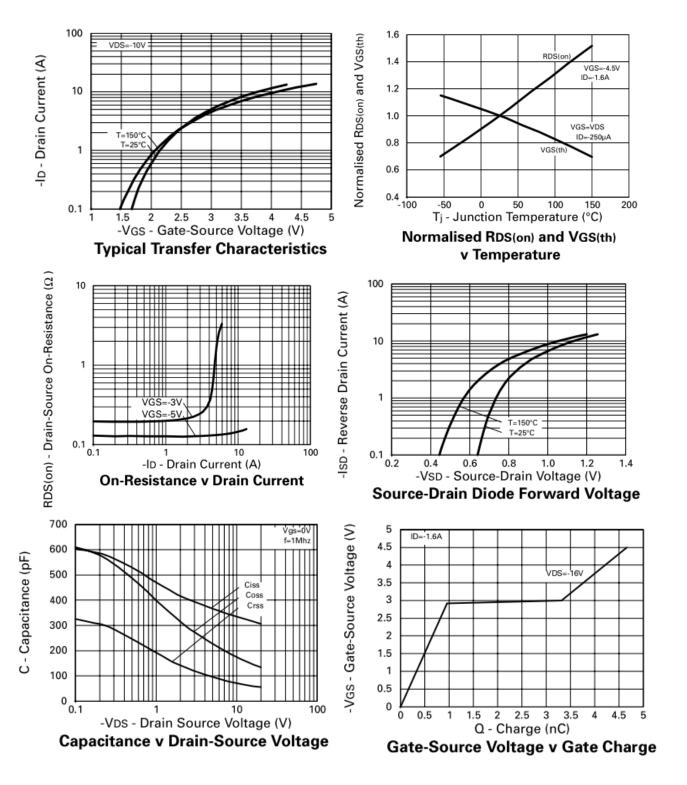
Notes:

- 5. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.
 6. For a device surface mounted on FR-4 PCB measured at t ≤ 5 secs.
 7. Repetitive rating pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.
 8. Measured under pulsed conditions. Width= 300µs; duty cycle ≤ 2%.
 9. Switching characteristics are independent of operating junction temperatures.
 10. For design aid only, not subject to production testing.



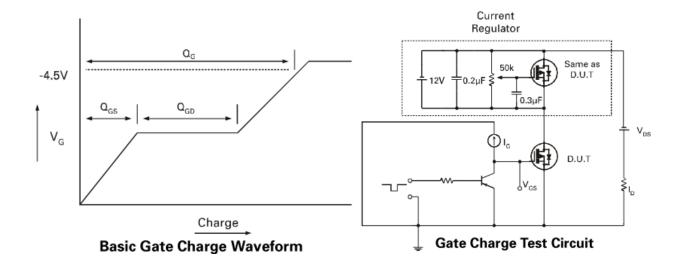


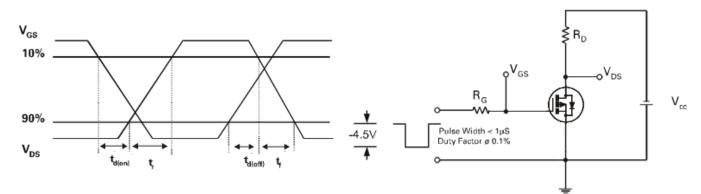






Test Circuits





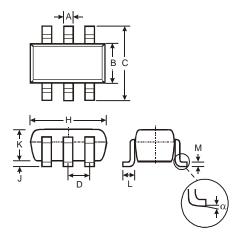
Switching Time Waveforms

Switching Time Test Circuit



Package Outline Dimensions

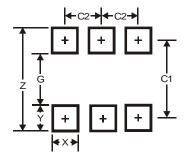
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT26							
Dim	Min	Max	Тур					
Α	0.35	0.50	0.38					
В	1.50	1.70	1.60					
С	2.70	3.00	2.80					
D		_	0.95					
Н	2.90	3.10	3.00					
J	0.013	0.10	0.05					
K	1.00	1.30	1.10					
L	0.35	0.55	0.40					
M	0.10	0.20	0.15					
α	0°	8°						
All D	imensi	ons in	mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95



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